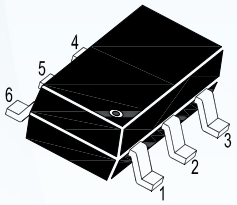
EVVOSEMI®
THINK CHANGE DO

ESD TVS MOS LDO Diode Sensor DC-DC

Product Specification

Domestic Part Number	2N7002DW
Overseas Part Number	2N7002DW
Equivalent Part Number	2N7002DW

N-Channel MOSFET



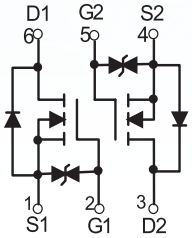
■ Features

- High density cell design for Low $R_{DS(on)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability
- ESD protected

■ Applications

- Load Switch for Portable Devices
- DC/DC Converter

■ Simplified outline (SOT-363)



$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
60 V	2.5Ω@10V	340mA
	3Ω@4.5V	

■ Absolute Maximum Ratings Ta = 25℃

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source voltage	60	V
V_{GS}	Gate-Source voltage	±20	V
I_D	Drain Current	340	mA
P_D	Power Dissipation	0.15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃
$R_{\theta JA}$	Thermal Resistance fromJunction to Ambient	833	℃ /W

N-Channel MOSFET

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static Characteristics						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0V, I_D =250μA	60			V
Gate Threshold Voltage*	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =1mA	1	1.3	2.5	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =48V,V_{GS} = 0V			1	μA
Gate –Source leakage current	I_{GSS1}	V_{GS} =±20V, V_{DS} = 0V			±10	μA
Drain-Source On-Resistance*	$R_{DS(on)}$	V_{GS} = 4.5V, I_D =200mA		1.1	3	Ω
		V_{GS} =10V,I_D =500mA		0.9	2.5	Ω
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=300mA			1.5	V
Recovered charge	Q_r	V_{GS}=0V,I_S=300mA,V_R=25V, dI_S/dt=-100A/μs		30		nC
Dynamic Characteristics**						
Input Capacitance	C_{iss}	V_{DS} =10V,V_{GS} =0V,f =1MHz			40	pF
Output Capacitance	C_{oss}				30	pF
Reverse Transfer Capacitance	C_{rss}				10	pF
Switching Characteristics**						
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V,V_{DD}=50V,R_G=50Ω, R_{GS}=50Ω, R_L=250Ω			10	ns
Turn-Off Delay Time	$t_{d(off)}$				15	ns
Reverse recovery Time	t_{rr}	V_{GS}=0V,I_S=300mA,V_R=25V, dI_S/dt=-100A/μs		30		ns
GATE-SOURCE ZENER DIODE						
Gate-Source Breakdown Voltage	BV_{GSO}	I_{gs}=±1mA (Open Drain)	±21.5		±30	V

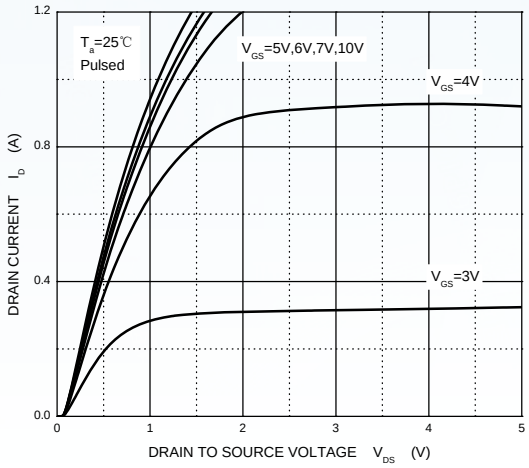
Notes :

*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%.

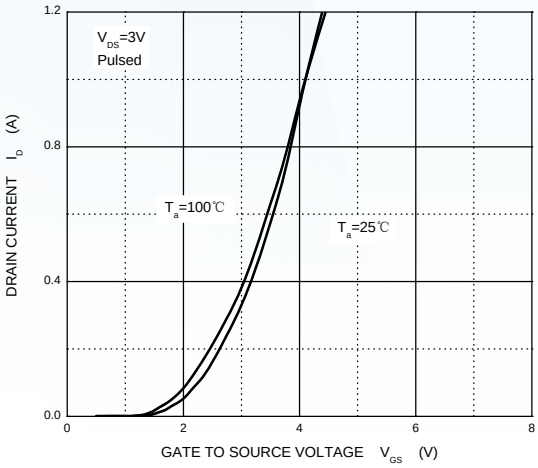
**These parameters have no way to verify.

N-Channel MOSFET

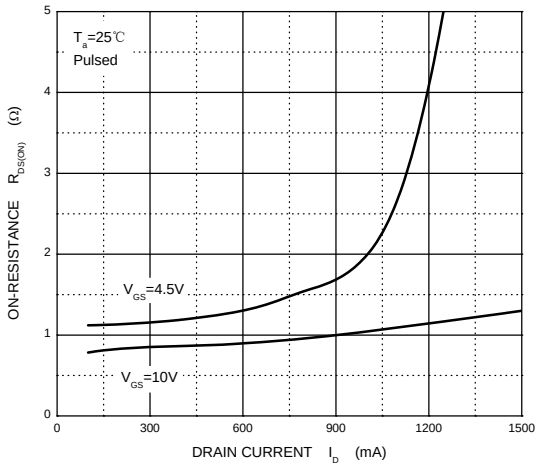
Output Characteristics



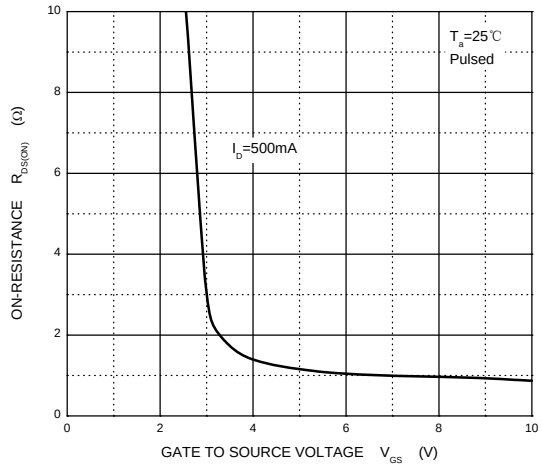
Transfer Characteristics



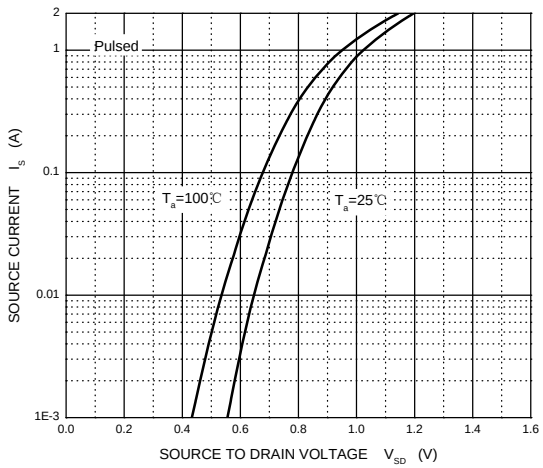
$R_{DS(ON)}$ — I_D



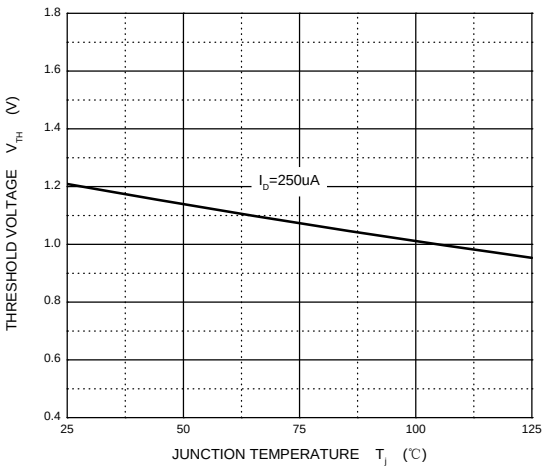
$R_{DS(ON)}$ — V_{GS}



I_S — V_{SD}

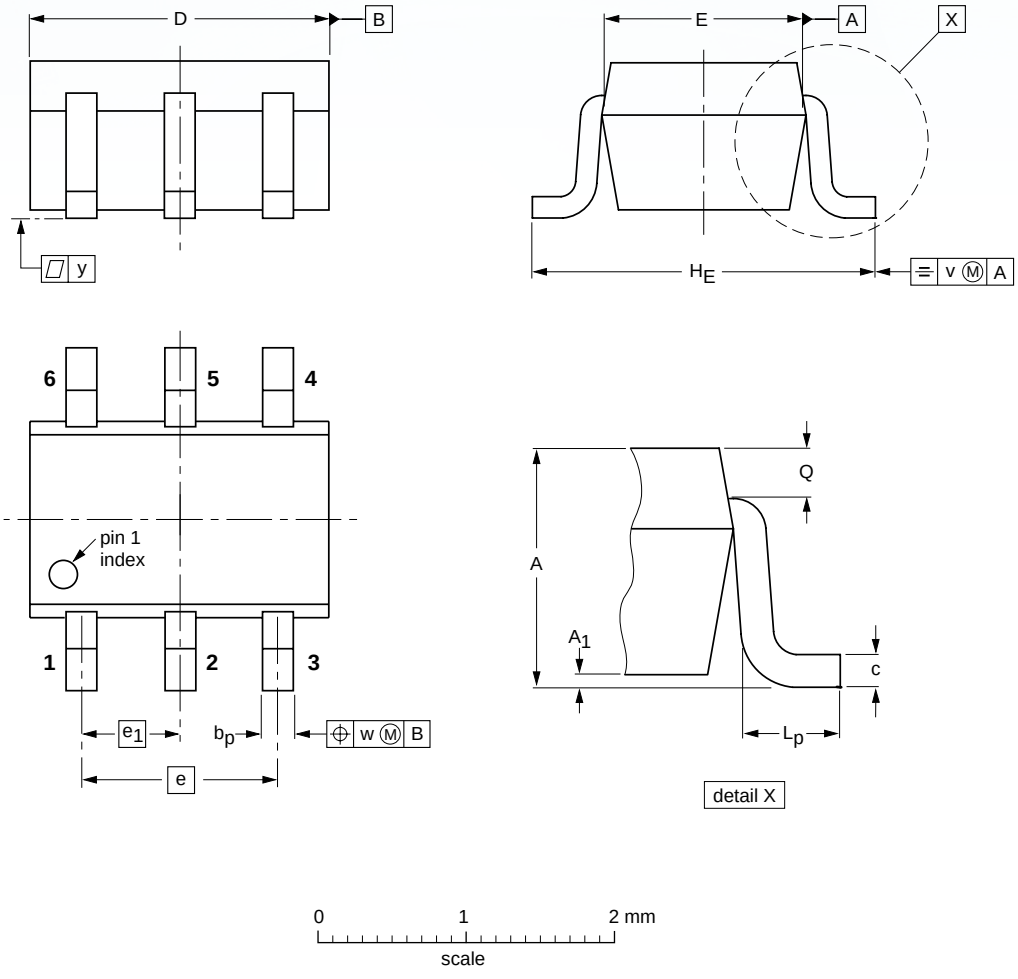


Threshold Voltage



N-Channel MOSFET

■ SOT-363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

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